

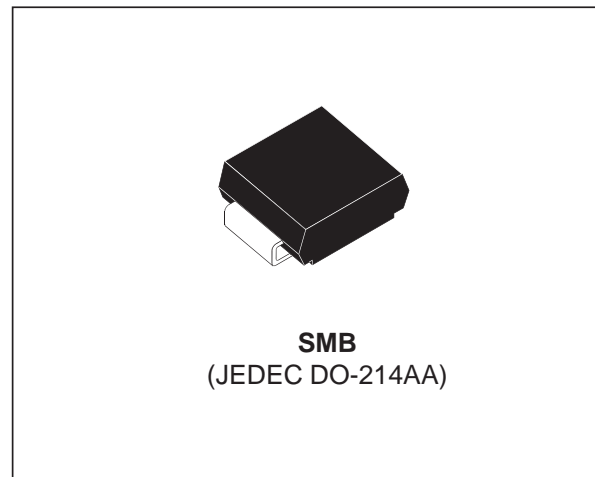
## LOW DROP POWER SCHOTTKY RECTIFIER

### MAIN PRODUCT CHARACTERISTICS

$I_{F(AV)}$	2 A
$V_{RRM}$	40 V
$T_j(\text{max})$	150 °C
$V_F(\text{max})$	0.34 V

### FEATURES AND BENEFITS

- VERY SMALL CONDUCTION LOSSES
- NEGLIGIBLE SWITCHING LOSSES
- LOW FORWARD VOLTAGE DROP
- SURFACE MOUNT MINIATURE PACKAGE
- AVALANCHE CAPABILITY SPECIFIED



### DESCRIPTION

Single chip Schottky rectifiers suited to Switched Mode Power Supplies and high frequency DC to DC converters.

Packaged in SMB, this device is especially intended for surface mounting and used in low voltage, high frequency inverters, free wheeling and polarity protection applications.

### ABSOLUTE RATINGS (limiting values)

Symbol	Parameter		Value	Unit
$V_{RRM}$	Repetitive peak reverse voltage		40	V
$I_{F(RMS)}$	RMS forward current		8	A
$I_{F(AV)}$	Average forward current	$T_L = 130^\circ\text{C} \quad \delta = 0.5$	2	A
$I_{FSM}$	Surge non repetitive forward current	$t_p = 10 \text{ ms}$ Sinusoidal	75	A
$P_{ARM}$	Repetitive peak avalanche power	$t_p = 1 \mu\text{s} \quad T_j = 25^\circ\text{C}$	2200	W
$T_{stg}$	Storage temperature range		- 65 to + 150	°C
$T_j$	Maximum operating junction temperature *		150	°C
$dV/dt$	Critical rate of rise of reverse voltage		10000	V/ $\mu\text{s}$

\* :  $\frac{dP_{tot}}{dT_j} < \frac{1}{R_{th(j-a)}}$  thermal runaway condition for a diode on its own heatsink

# STPS2L40U

## THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
$R_{th(j-l)}$	Junction to lead	SMB	20	°C/W

## STATIC ELECTRICAL CHARACTERISTICS

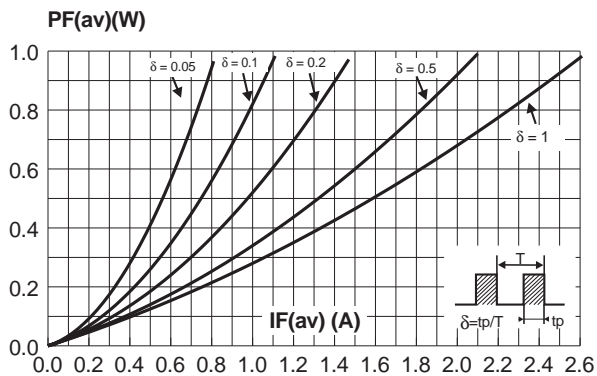
Symbol	Tests Conditions	Tests Conditions	Min.	Typ.	Max.	Unit
$I_R^*$	Reverse leakage current	$T_j = 25^\circ\text{C}$	$V_R = 40\text{ V}$		220	$\mu\text{A}$
		$T_j = 100^\circ\text{C}$			20	mA
		$T_j = 125^\circ\text{C}$		38	80	mA
$V_F^*$	Forward voltage drop	$T_j = 25^\circ\text{C}$	$I_F = 1\text{ A}$		0.39	V
		$T_j = 125^\circ\text{C}$		0.25	0.28	
		$T_j = 25^\circ\text{C}$	$I_F = 2\text{ A}$		0.43	V
		$T_j = 125^\circ\text{C}$		0.31	0.34	
		$T_j = 25^\circ\text{C}$	$I_F = 4\text{ A}$		0.5	V
		$T_j = 125^\circ\text{C}$		0.39	0.45	

Pulse test : \*  $t_p = 380\mu\text{s}$ ,  $\delta < 2\%$

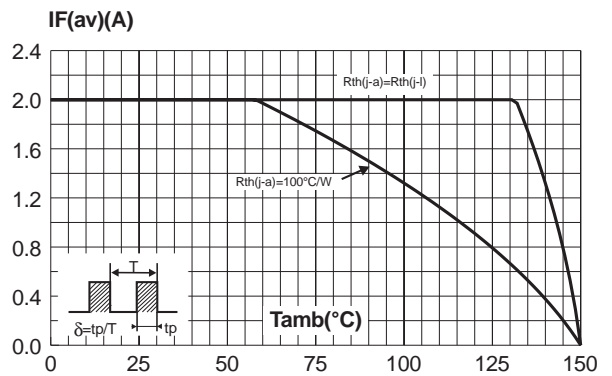
To evaluate the maximum conduction losses use the following equation :

$$P = 0.22 \times I_{F(AV)} + 0.06 I_{F(RMS)}^2$$

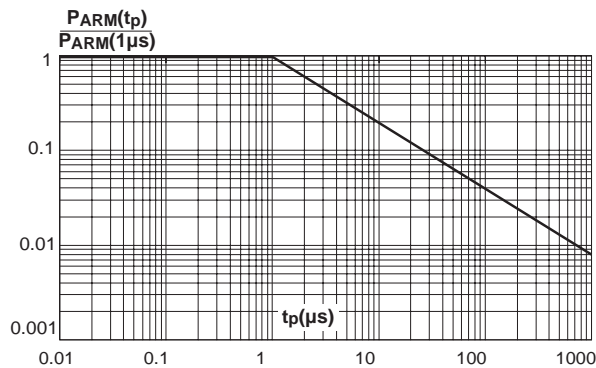
**Fig. 1:** Average forward power dissipation versus average forward current.



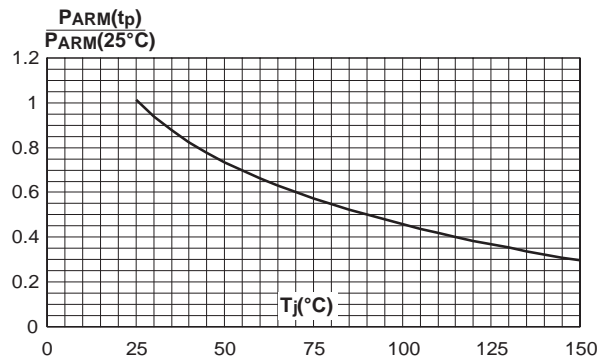
**Fig. 2:** Average forward current versus ambient temperature ( $\delta=0.5$ ).



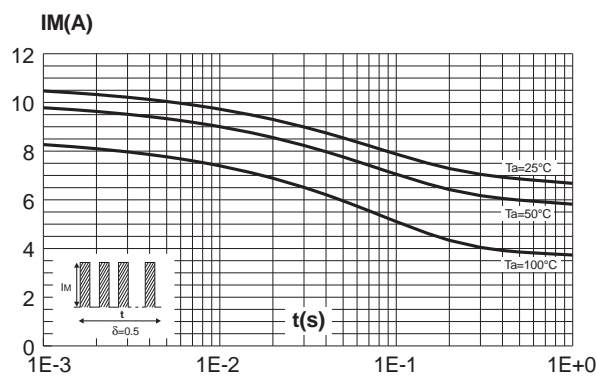
**Fig. 3:** Normalized avalanche power derating versus pulse duration.



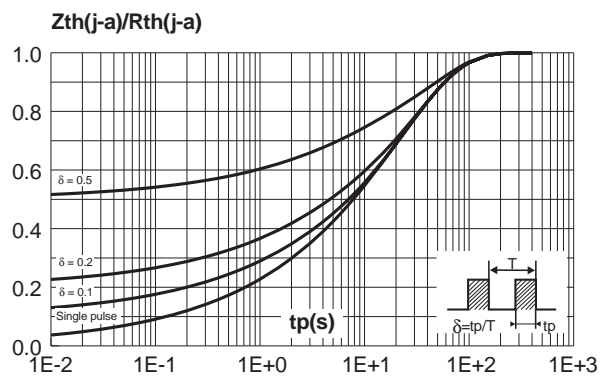
**Fig. 4:** Normalized avalanche power derating versus junction temperature.



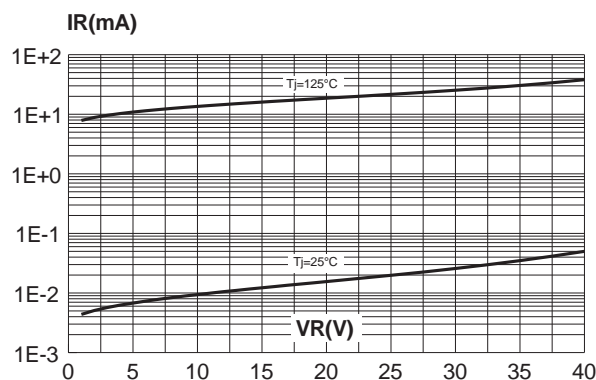
**Fig. 5:** Non repetitive surge peak forward current versus overload duration (maximum values).



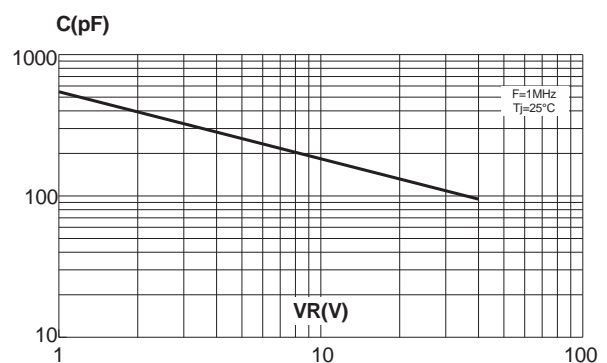
**Fig. 6:** Relative variation of thermal impedance junction to ambient versus pulse duration.



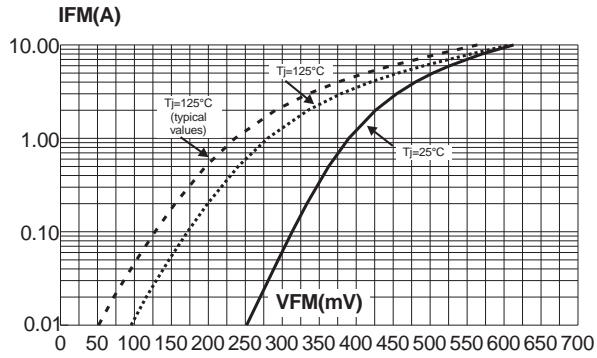
**Fig. 7:** Reverse leakage current versus reverse voltage applied (typical values).



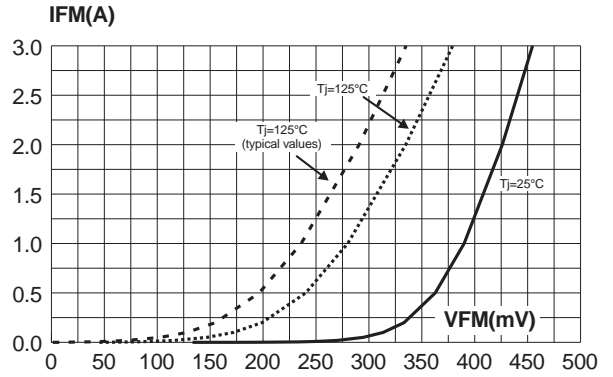
**Fig. 8:** Junction capacitance versus reverse voltage applied (typical values).



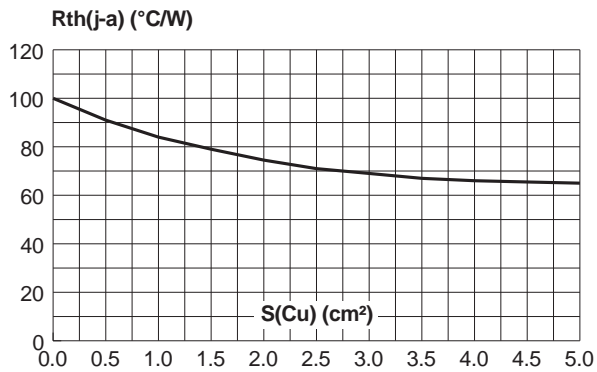
**Fig. 9-1:** Forward voltage drop versus forward current (maximum values, high level).



**Fig. 9-2:** Forward voltage drop versus forward current (maximum values, low level).

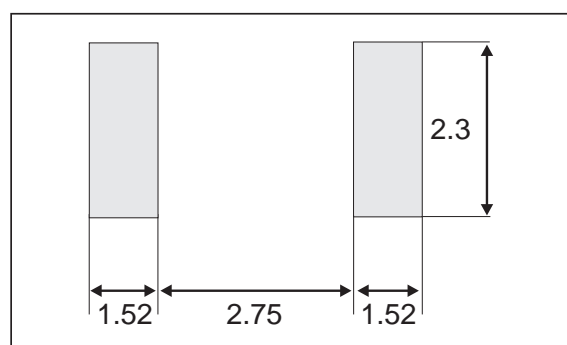


**Fig. 10:** Thermal resistance junction to ambient versus copper surface under each lead (Epoxy printed circuit board FR4, copper thickness  $s(\text{Cu}) = 35\mu\text{m}$ )



**PACKAGE MECHANICAL DATA**  
**SMB**

REF.	DIMENSIONS			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A1	1.90	2.45	0.075	0.096
A2	0.05	0.20	0.002	0.008
b	1.95	2.20	0.077	0.087
c	0.15	0.41	0.006	0.016
E	5.10	5.60	0.201	0.220
E1	4.05	4.60	0.159	0.181
D	3.30	3.95	0.130	0.156
L	0.75	1.60	0.030	0.063

**FOOT PRINT DIMENSIONS (in millimeters)**


Ordering type	Marking	Package	Weight	Base qty	Delivery mode
STPS2L40U	GD4	SMB	0.107g	2500	Tape & reel

- BAND INDICATES CATHODE
- EPOXY MEETS UL94,V0

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